

Phase Control Thyristors (Hockey PUK Version), 990 A



B-PUK (TO-200AC)

PRIMARY CHARACTERISTICS					
I _{T(AV)}	990 A				
V _{DRM} /V _{RRM}	800 V, 1200 V, 1400 V, 1600 V, 1800 V, 2000 V				
V _{TM}	1.62 V				
I _{GT}	100 mA				
T _J	-40 °C to +125 °C				
Package	B-PUK (TO-200AC)				
Circuit configuration	Single SCR				

FEATURES

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case B-PUK (TO-200AC)



- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
		990	A			
I _{T(AV)}	T _{hs}	55	°C			
1		2000	A			
I _{T(RMS)}	T _{hs}	25	°C			
	50 Hz	17 800	Δ.			
I _{TSM}	60 Hz	18 700	Α			
l ² t	50 Hz	1591	kA ² s			
1-1	60 Hz	1452	KA-S			
V _{DRM} /V _{RRM}		800 to 2000	V			
t _q	Typical	150	μs			
TJ		-40 to 125	°C			

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$\begin{split} I_{DRM}/I_{RRM} & \text{MAXIMUM AT} \\ T_J &= T_J & \text{MAXIMUM} \\ & \text{mA} \end{split}$				
	08	800	900					
VS-ST730CL	12	1200	1300					
	14	1400	1500	80				
	16	1600	1700	60				
	18	1800	1900					
	20	2000	2100					



ABSOLUTE MAXIMUM RATINGS	3					
PARAMETER	SYMBOL		TEST CONDITIONS			
Maximum average on-state current	L	180° condu	ction, half sine v	wave	990 (375)	Α
at heatsink temperature	I _{T(AV)}	double side	(single side) co	oled	55 (85)	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink tempe	erature double side cooled	2000	
		t = 10 ms	No voltage		17 800	
Maximum peak, one-cycle	1	t = 8.3 ms	reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	18 700	A kA ² s
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		15 000	
		t = 8.3 ms	reapplied		15 700	
Marrian II fan fan fan i		t = 10 ms	No voltage reapplied		1591	
	l ² t	t = 8.3 ms			1452	
Maximum I ² t for fusing		t = 10 ms	100 % V _{RRM}		1125	
		t = 8.3 ms	reapplied		1027	
Maximum $I^2\sqrt{t}$ for fusing	I ² √t	t = 0.1 to 10) ms, no voltage	reapplied	15 910	kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x \ I_{T(AV)} < I < \pi \ x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.98	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			v
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			0.32	mΩ
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.27	11152
Maximum on-state voltage	V_{TM}	$I_{pk} = 2000 A$	$\Lambda, T_J = T_J \text{ maxim}$	um, t _p = 10 ms sine pulse	1.62	V
Maximum holding current	Ι _Η	T. – 25 °C	anode supply 1	2 V resistive load	600	mA
Typical latching current	lμ	T _J = 25 °C, anode supply 12 V resistive load			1000	I IIIA

SWITCHING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/μs			
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1$ A/ μ s $V_d = 0.67 \% V_{DRM}$, $T_J = 25 °C$	1.0				
Typical turn-off time	t _q	$\begin{aligned} I_{TM} = 750 \text{ A, } T_J = T_J \text{ maximum, dI/dt} = 60 \text{ A/}\mu\text{s,} \\ V_R = 50 \text{ V, dV/dt} = 20 \text{ V/}\mu\text{s, gate 0 V 100 }\Omega, t_p = 500 \mu\text{s} \end{aligned}$	150	μs			

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = T _J maximum linear to 80 % rated V _{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	80	mA



TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
FANAMETEN	STIVIBOL	I Ex	31 CONDITIONS	Тур.	Max.	UNITS
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	$t_p \leq 5 \ ms$	10	0.0	W
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	VV
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	3	.0	Α
Maximum peak positive gate voltage	+ V _{GM}	T - T movimum	+ < 5 ma	2	.0	V
Maximum peak negative gate voltage	- V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms			.0]
		T _J = -40 °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units	200	-	mA
DC gate current required to trigger	I _{GT}	T _J = 25 °C		100	200	
		T _J = 125 °C		50	-	
		T _J = -40 °C		2.5	-	
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C	12 V anode to cathode applied	1.8	3.0	V
		T _J = 125 °C		1.1	-	
DC gate current not to trigger	I _{GD}	T T	Maximum gate current/voltage not to trigger is the maximum	1	0	mA
DC gate voltage not to trigger	V _{GD}	T _J =T _J maximum value which will not trige unit with rated V _{DRM} and cathode applied		0.	25	٧

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	T_{J}		-40 to 125	°C		
Maximum storage temperature range	T _{Stg}		-40 to 150			
Maximum thermal resistance, junction to heatsink	В	DC operation single side cooled	0.073			
Maximum thermal resistance, junction to heatsink	R _{thJ-hs}	DC operation double side cooled	0.031	K/W		
Maximum thermal resistance, case to heatsink	В	DC operation single side cooled	0.011	IV VV		
iviaximum thermal resistance, case to heatsink	R _{thC-hs}	DC operation double side cooled	0.006			
Mounting force, ± 10 %			14 700 (1500)	N (kg)		
Approximate weight			255	g		
Case style		See dimensions - link at the end of datasheet	B-PUK (TO-			

△R _{thJ-hs} CONDUCTION							
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEGT COMPLETIONS	LIMITO	
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS	
180°	0.009	0.009	0.006	0.006	$T_J = T_J$ maximum		
120°	0.011	0.011	0.010	0.011			
90°	0.014	0.014	0.015	0.015		K/W	
60°	0.020	0.020	0.021	0.021			
30°	0.036	0.036	0.036	0.036			

Note

The table above shows the increment of thermal resistance RthJ-hs when devices operate at different conduction angles than DC

www.vishay.com

Vishay Semiconductors

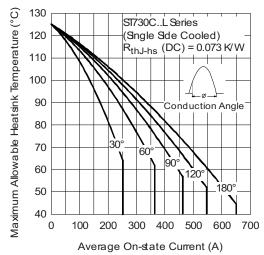


Fig. 1 - Current Ratings Characteristics

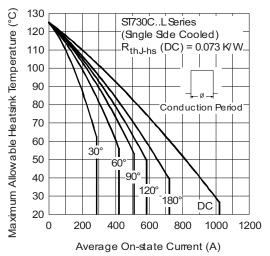


Fig. 2 - Current Ratings Characteristics

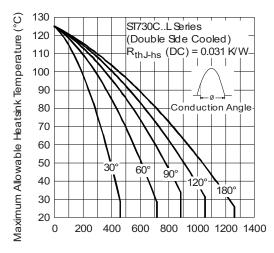


Fig. 3 - Current Ratings Characteristics

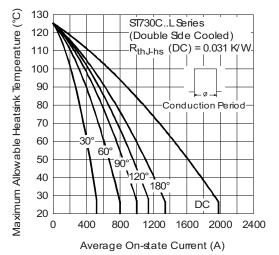


Fig. 4 - Current Ratings Characteristics

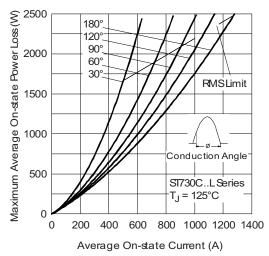


Fig. 5 - On-State Power Loss Characteristics

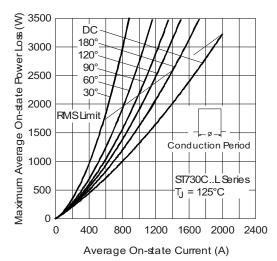


Fig. 6 - On-State Power Loss Characteristics

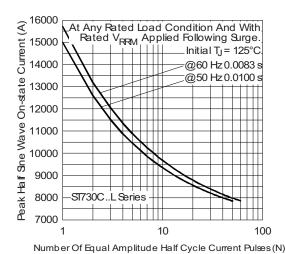


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

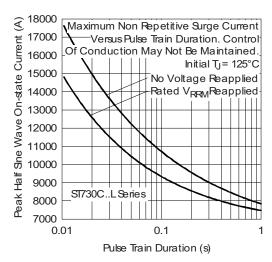


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

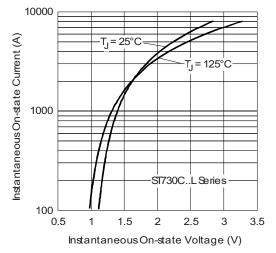


Fig. 9 - On-State Voltage Drop Characteristics

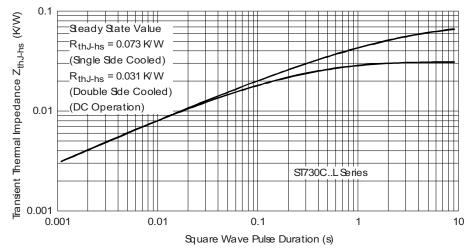


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics



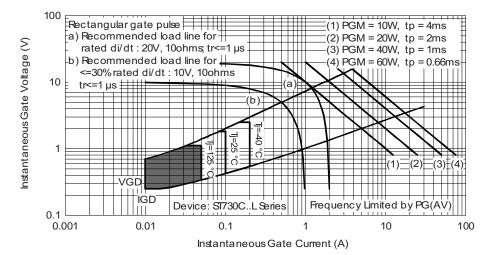
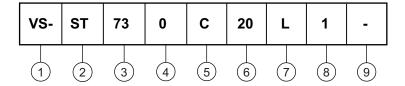


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device	e code
DEVIC	e coue



1 - Vishay Semiconductors product

2 - Thyristor

3 - Essential part number

4 - 0 = converter grade

5 - C = ceramic PUK

6 - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)

7 - L = PUK case B-PUK (TO-200AC)

8 - 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = eyelet terminals (gate and auxiliary cathode soldered leads)

3 = fast-on terminals (gate and auxiliary cathode soldered leads)

9 - Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

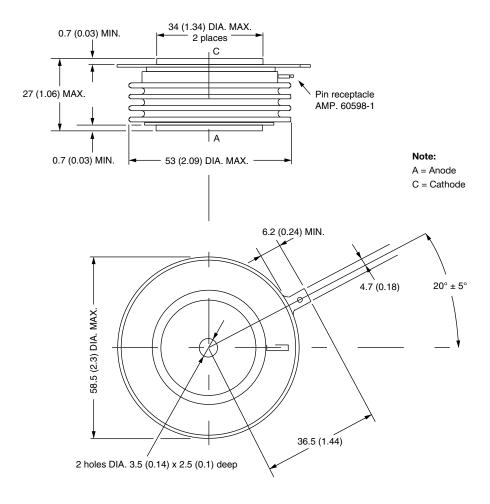
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95076			



B-PUK (TO-200AC)

DIMENSIONS in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)

Legal Disclaimer Notice



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.